

# High-speed switching diode

## Features

1. Small surface mounting type, fits onto SOD 323/SOT 23 footprints
2. High Speed
3. High reliability with high surge current handling capability



## Applications

High speed switching

## Construction

Silicon epitaxial planar

## Absolute Maximum Ratings

$T_a=25^{\circ}\text{C}$

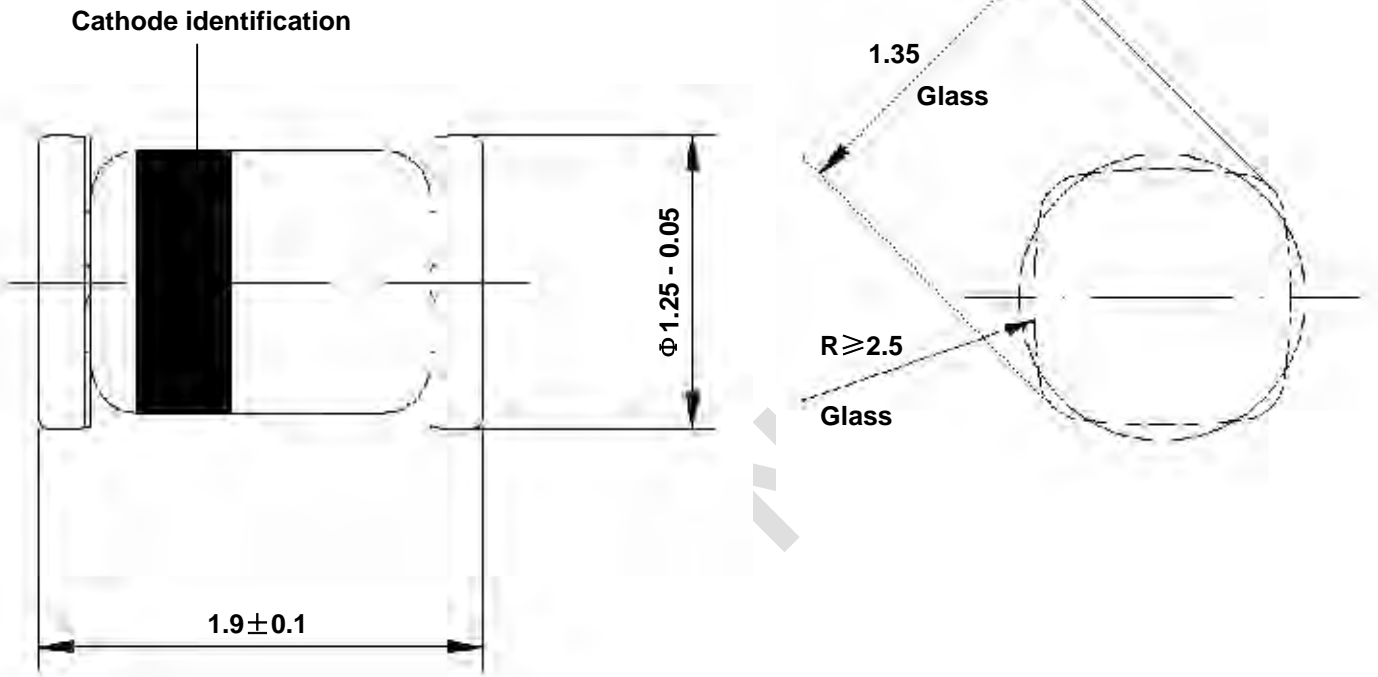
Parameter	Symbol	Limits	Unit
Peak reverse voltage	$V_{RM}$	90	V
DC reverse voltage	$V_R$	80	V
Peak forward current	$I_{FM}$	225	mA
Mean rectifying current	$I_o$	100	mA
Surge current (1s)	$I_{surge}$	500	mA
Junction temperature	$T_j$	125	$^{\circ}\text{C}$
Storage temperature	$T_{stg}$	-55~+125	$^{\circ}\text{C}$

## Electrical Characteristics

$T_a=25^{\circ}\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_F$	-	0.94	1.2	V	$I_F=100\text{mA}$
Reverse current	$I_R$	-	0.03	0.1	$\mu\text{A}$	$V_R=80\text{V}$
Capacitance between terminals	$C_T$	-	0.72	3.0	pF	$V_R=0.5\text{V}, f=1\text{MHz}$
Reverse recovery time	$t_{rr}$	-	1.2	4.0	ns	$V_R=6\text{V}, I_F=10\text{mA}, R_L=100$

## Dimensions in mm



Glass Case  
Micro Melf

WEJ ELEC

### Characteristics (Ta=25°C unless specified otherwise)

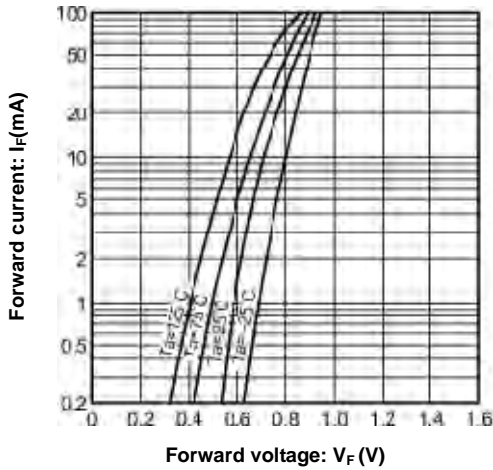


Figure 1. Forward characteristics

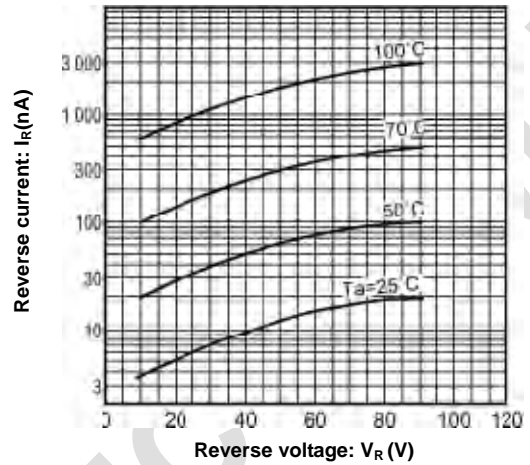


Figure 2. Reverse characteristics

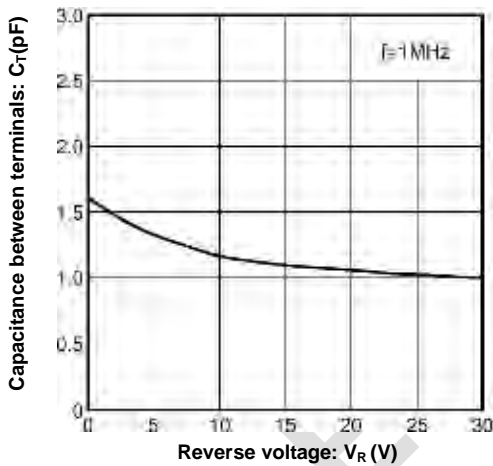


Figure 3. Capacitance between terminals characteristics

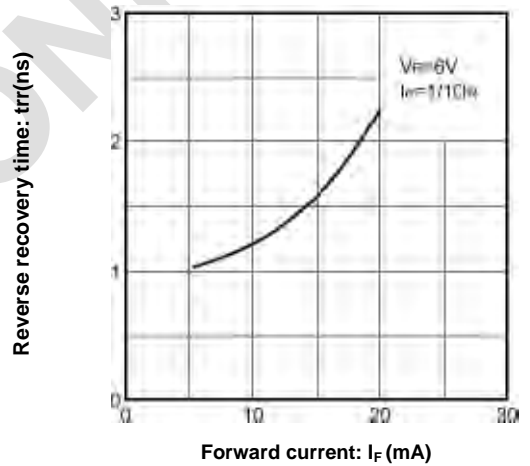


Figure 4. Reverse recovery time characteristics

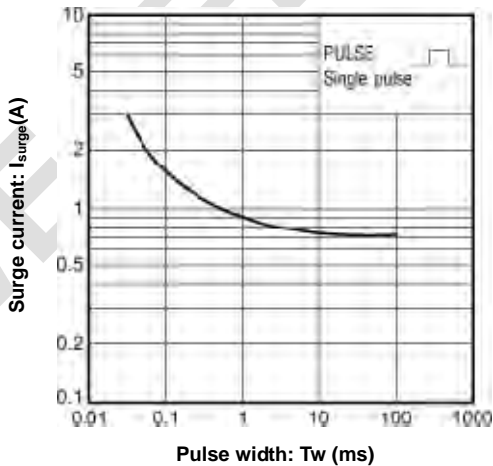


Figure 5. Surge current characteristics

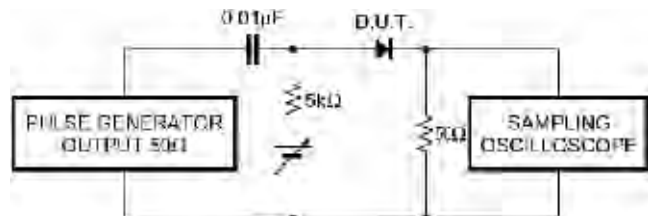


Figure 6. Reverse recovery time (trr) measurement circuit